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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 6

Complete if Known	
Application Number	10/786,643
Filing Date	2/25/2004
First Named Inventor	Cheng, *et al.*
Art Unit	2826
Examiner Name	Quinto, Kevin
Attorney Docket Number	TSM03-0698

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
KQ	1	US-4,069,094	01-17-1978	Shaw et al.	
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Examiner Signature	Kevin Quinto	Date Considered	4/28/05

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Examiner Signature	Kevin Quinto	Date Considered	11/20/05

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Sheet 3 of 6

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Filing Date	2/25/2004
First Named Inventor	Cheng, *et al.*
Art Unit	2826
Examiner Name	Quinto, Kevin
Attorney Docket Number	TSM03-0698

FOREIGN PATENT DOCUMENTS

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KQ	78	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

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Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Examiner Signature	Kevin Quinto	Date Considered	11/20/05

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Sheet 4 of 6

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Application Number	10/786,643
Filing Date	2/25/2004
First Named Inventor	Cheng, *et al.*
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Attorney Docket Number	TSM03-0698

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Examiner Signature	Kevin Quinto	Date Considered	4/20/05

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KQ	94	LEITZ, C.W., *et al.*, "Hole Mobility Enhancements In Strained $Si/Si_{1-Y}Ge_Y$ P-Type Metal-Oxide-Semiconductor Field-Effect Transistors Grown On Relaxed $Si_{1-X}Ge_X$ (x<y) Virtual Substrates," Applied Physics Letters, Vol. 79, No. 25, December 17, 2001, pp. 4246-4248.	
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